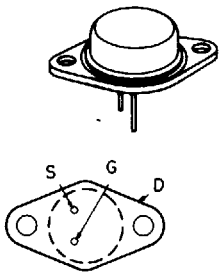



Power MOSFETS

ECG Type	Description and Application	Transconductance gfs mhos	Drain to Source Breakdown Voltage BV _{DSS}	Gate to Source Breakdown Voltage BV _{GS}	Continuous Drain Current I _D Amps	Gate to Source Cutoff Voltage V _{GS} (off)	Drain to Source Resistance ^r DS (on) Ohms	Input Cap C _{iss} pf	Device Dissipation @T _C = 25°C PD Watts	Package	
										Case/ Fig./ Basing	
ECG2392 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	6 Min	100 Min	± 20 Max*	32	4 Max	.06 Max	1500 Typ	125 Max	TO-3 Fig. T28	
ECG2386 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	2 Min	600 Min	± 20 Max*	6	4.5 Max	1.2 Max	1800 Max	150 Max		
ECG2384 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	1.8 Min	800 Min	± 20 Max*	6	4 Max	1.5 Max	3500 Max	125 Max		
ECG2390 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	3 Min	60 Min	± 20 Max*	12	4.5 Max	.2 Max	800 Max	75 Max	TO-220 Fig. T41	
ECG2382 ▲ (Compl to ECG2383)	MOSFET, N-Ch, Enhancement Hi Speed Switch	1.5 Min	100 Min	± 20 Max*	8	4 Max	.5 Max	750 Max	75 Max		
ECG2383 ▲ (Compl to ECG2382)	MOSFET, P-Ch, Enhancement Hi Speed Switch	2 Min	100 Min	± 20 Max*	8	4.5 Max	.4 Max	1200 Max	75 Max		
ECG66 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	3 Min	100 Min	± 20 Max*	12	4.5 Max	.18 Max	1200 Max	75 Max		
ECG2388 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	5 Min	200 Min	± 20 Max*	12.5	4 Max	.2 Max	1000 Typ	75 Max		
ECG67 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	2 Min	400 Min	± 20 Max*	5	4.5 Max	1.5 Max	1200 Max	75 Max		
ECG2380 ▲ (Compl to ECG2381)	MOSFET, N-Ch, Enhancement Hi Speed Switch	1 Min	500 Min	± 20 Max*	2	4.5 Max	4 Max	500 Max	75 Max		
ECG2381 ▲ (Compl to ECG2380)	MOSFET, P-Ch, Enhancement Hi Speed Switch	.5 Min	500 Min	± 20 Max*	2	4.5 Max	6 Max	1000 Max	75 Max		
ECG2385 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	5 Min	500 Min	± 30 Max*	8	4 Max	.8 Max	1800 Max	125 Max		
ECG2387 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	3 Min	800 Min	± 30 Max*	4	4 Max	3 Max	1250 Max	125 Max		

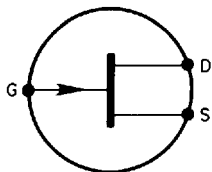
* Warning - Exceeding BV_{GS} maximum will result in permanent damage to the gate region oxide layer.

▲ Refer to MOSFET Handling Precautions - Page 1-31

Package Outline - See Page 1-76

FET and MOSFET Diagrams (Observe MOS Handling) ▲

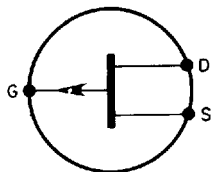
Depletion N-Ch JFET



ECG

312 456
451 457 461 (Dual) 468
452 458 466 469
453 459 467

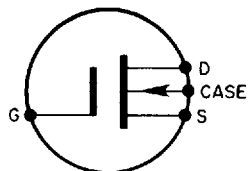
Depletion P-Ch JFET



ECG

326
460
489

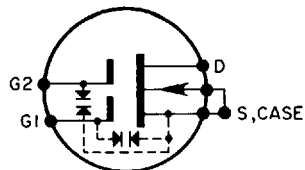
Depletion N-Ch MOSFET



ECG

220
462

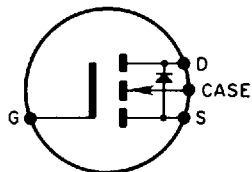
Dual Gate Depletion N-Ch MOSFET



ECG

221
222 (Gate Protected)
454 (Gate Protected)
455 (Gate Protected)

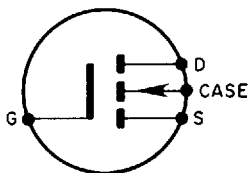
Enhancement N-Ch MOSFET



ECG

66 2382 2386 2390
67 2384 2387 2392
2380 2385 2388

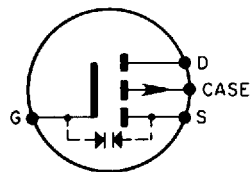
Enhancement N-Ch MOSFET



ECG

465

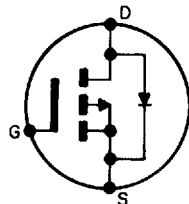
Enhancement P-Ch MOSFET



ECG

463 (Dual)
(Gate Protected)
464

Enhancement P-Ch MOSFET



ECG

2381
2382